

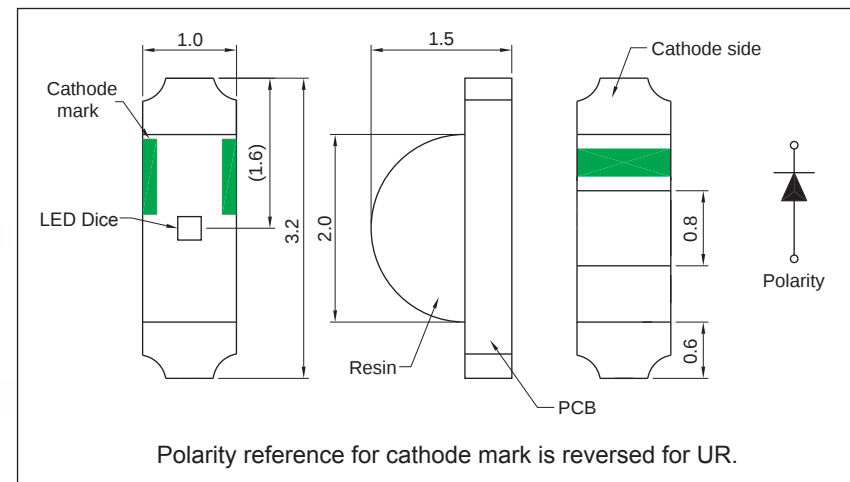
Features

- Chip LED (3.2x1.5x1.0)
- Super compact

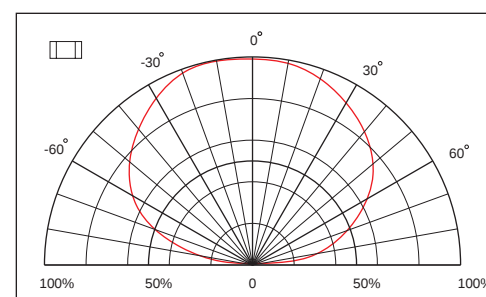
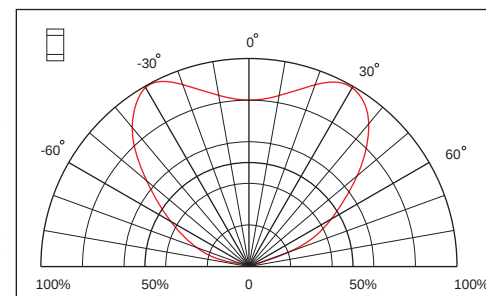


Package Outline Dimensions

(Unit:mm Tolerance:±0.1)

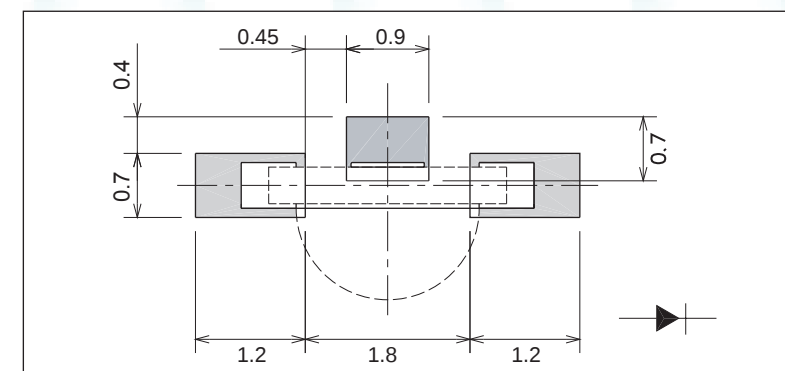


Directive Characteristics



Recommended Soldering Pattern

Unit: mm



Absolute Maximum Ratings

(Ta=25°C)

Item	Symbol	GaP	GaAsP	AlGaAs	AlInGaP	InGaN	Unit
Power Dissipation	P _D	65	65	66	72	78	mW
DC Forward Current	I _F	25	25	30	30	20	mA
Pulsed Forward Current	I _{FP} *	100	100	100	100	80	mA
Reverse Voltage	V _R	5					V
Operating Temperature	T _{OP}	-30 to 80					°C
Storage Temperature	T _{ST}	-40 to 85					°C

* 0.1msec pulse, 10% duty cycle.

Electrical / Optical Characteristics

(Ta=25°C)

Part Number	Emitting color	Material	Forward Voltage(V _F)		Wavelength (nm) typ.			Luminous Intensity (mcd)*		I _F (mA)	Viewing Angle 2θ _{1/2}
			typ.	max.	λ _D	λ _P	Δλ	min.	typ.		
HT-110YG	Yellow Green	GaP	2.2	2.6	573	568	30	9	16	20	x=140 y=120
HT-110Y	Yellow	GaAsP	2.1	2.6	590	589	35	5.6	9	20	x=140 y=120
HT-110D	Amber	GaAsP	2.1	2.6	608	610	35	5.6	9	20	x=140 y=120
HT-110SD	Super Bright Orange	GaAsP	2.1	2.6	629	642	35	3.6	9	20	x=140 y=120
HT-110UR	Super Bright Red	AlGaAs	1.8	2.2	643	660	20	9	20	20	x=140 y=120
HT-110UYG	Ultra Bright Yellow Green	AlInGaP	2.0	2.4	573	574	20	36	60	20	x=140 y=120
HT-110UY	Ultra Bright Yellow	AlInGaP	1.9	2.4	589	593	15	36	120	20	x=140 y=120
HT-110UD	Ultra Bright Amber	AlInGaP	1.9	2.4	605	609	17	56	160	20	x=140 y=120
HT-110USD	Ultra Bright Orange	AlInGaP	1.9	2.4	622	636	17	56	120	20	x=140 y=120
HT-110NB	Blue	InGaN	3.3	3.9	470	468	40	36	60	20	x=140 y=120
HT-110NG	Green	InGaN	3.3	3.9	527	520	40	140	226	20	x=140 y=120
HT-110TW	White	InGaN	3.3	3.9	x=0.29 y=0.31	-	-	90	180	20	x=140 y=120
HT-110NB5	Blue	InGaN	2.8	3.15	472	470	40	9	26	5	x=140 y=120
HT-110NG5	Green	InGaN	2.8	3.15	529	522	40	25	50	5	x=140 y=120
HT-110TW5	White	InGaN	2.8	3.15	x=0.29 y=0.32	-	-	40	70	5	x=140 y=120

*Per NIST standards

